



DCR3620M65

Phase Control Thyristor

Replaces DS6388-1 DS6388-2 March 2022 (LN41625)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Crowbar
- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
DCR3620M65* DCR3620M60 DCR3620M55	6500 6000 5500	T_{vj} = -40°C to 125°C, IDRM = $IRRM$ = 300mA, $VDRM$, $VRRM$ t_p = 10ms VDSM & $VRSM$ = VDRM & $VRRM$ + 100V respectively

Lower voltage grades available.

KEY PARAMETERS

\mathbf{V}_{DRM}	6500V
I _{T(AV)}	3620A
Ітѕм	44700A
dV/dt*	2000V/μs
dl/dt	500A/μs

^{*} Higher dV/dt selections are available on request

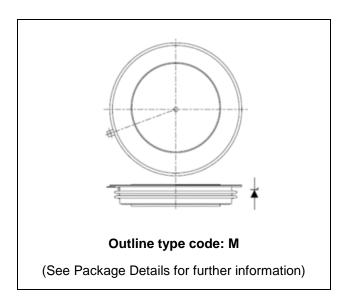


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR3620M65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

www.dynexsemi.com 1/10

^{*6200}V @ -40°C, 6500V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
İT(AV)	Mean on-state current	Half wave resistive load	3620	А
IT(RMS)	RMS value	-	5690	А
lτ	Continuous (direct) on-state current	-	5320	Α

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	44.7	kA
l²t	I ² t for fusing	V _R = 0	9.99	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	Test Conditions		Max.	Units
		Double side cooled	DC	-	5.2	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cingle side and a	Anode DC	-	10.1	°C/kW
		Single side cooled	Cathode DC	-	10.8	°C/kW
Date 15	The word resistance are to be established	Clamping force 83kN	Double side	-	1.0	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	2.0	°C/kW
Tvj	Tvj Virtual junction temperature Blocking VDRM / VR			-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			74	91	kN

www.dynexsemi.com 2/10



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Тур.	Max.	Units
1/1	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C		300	mA
IRRM/IDRM	Peak reverse and oir-state current	At 50% VRRM/VDRM, Tcase = 125°C	20	-	mA

Symbol	Parameter	Parameter Test Conditions		Min.	Max.	Units
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.80	2.05	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% VdRM, Tj = 125°C, g	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x IT(AV)	Repetitive 50Hz	-	200	A/µs
di/dt	Rate of fise of on-state current	Gate source 30V, 10Ω tr < 0.5 μ s, Tj = 125°C	Non-repetitive	-	500	A/µs
V T(TO)	Threshold voltage - Low level	500A to 3300A at Tcase = 1	25°C	-	0.93	V
V T(TO)	Threshold voltage - High level	3300A to 9000A at Tcase = 125°C			1.16	٧
	On-state slope resistance - Low level	500A to 3300A at Tcase = 125°C			0.29	mΩ
ľτ	On-state slope resistance - High level	3300A to 9000A at Tcase = 1	-	0.22	mΩ	
tgd	Delay time	$V_D = 67\% \ V_{DRM}$, gate source $t_r = 0.5 \mu s$, $T_j = 25^{\circ}C$	e 30V, 10Ω	-	3	μs
tq	Turn-off time	Tr = 3000A, Tj = 125°C, VR = 200V, $dI/dt = 1A/\mu s, dV_{DR}/dt = 20V/\mu s linear$		-	500	μs
Qs	Stored charge	I _T = 1500A, T _j = 125°C, dl/dt = 1A/μs		4540	8620	μC
IRR	Reverse recovery current	V _R ~ 2600V, C _S = 1μF, R _S =	63Ω	56	80	Α
l _L	Latching current	Tj = 25°C, V _D = 5V		-	3	А
Ін	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 50	0Α, Iτ = 5Α	-	300	mA

www.dynexsemi.com 3/10



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol Parameter		Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Iст Gate trigger current		VDRM = 5V, Tcase = 25°C	400	mA
Igp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

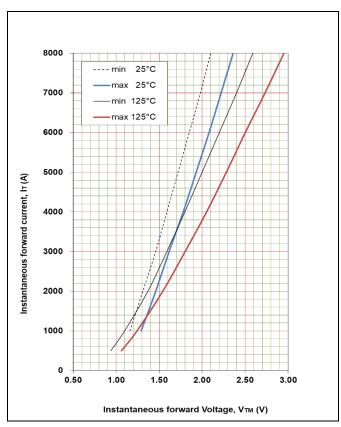


Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = -0.632454

B = 0.283028

C = 0.000246

D = -0.010394

These values are valid for $T_j = 125$ °C for $I_T 500A$ to 9000A

www.dynexsemi.com 4/10



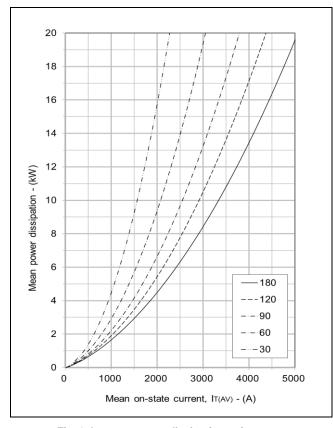


Fig. 3 On-state power dissipation - sine wave

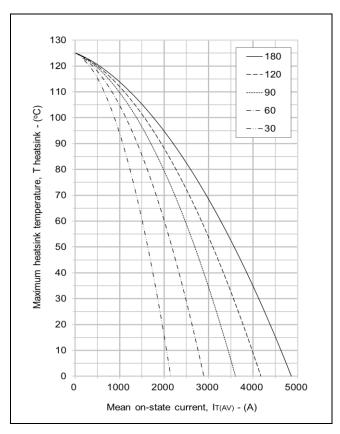


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

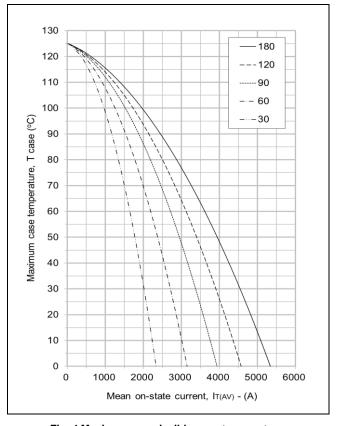


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

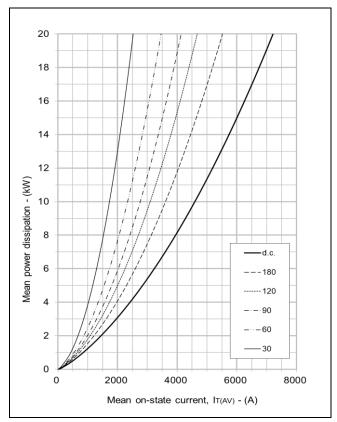


Fig. 6 On-state power dissipation - rectangular wave

www.dynexsemi.com 5/10



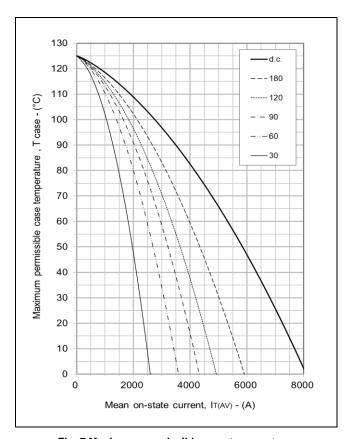
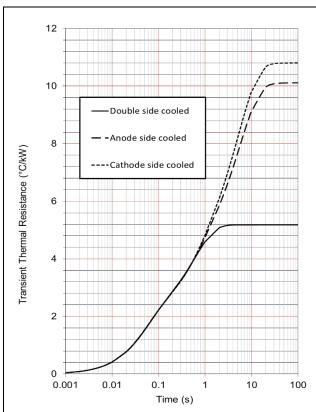


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



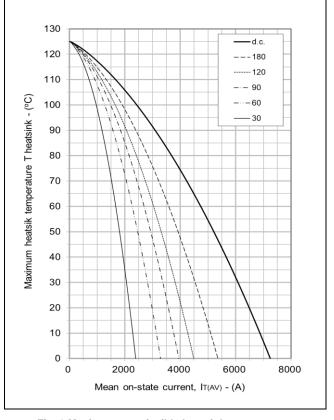


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	1.995	1.243	1.945	0.005
cooled	Ti(s)	0.050	0.593	0.592	110.511
Anode side	Ri(°C/kW)	6.093	1.957	2.042	0.036
cooled	Ti(s)	5.460	0.511	0.050	110.174
Cathode side	Ri(°C/kW)	6.857	1.876	2.063	0.025
cooled	Ti(s)	5.181	0.557	0.050	110.155

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}(j-c)}$ when the device operates at conduction angles other than d.c.

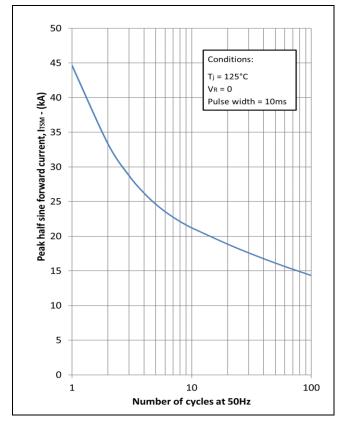
Double side cooling				Ai	node Side	Cooling
	ΔZ_{th}	ΔZ _{th} (Z)			ΔZ_t	_h (Z)
θ°	sine.	rect.		θ°	sine.	rect
180	0.51	0.36		180	0.51	0.36
120	0.57	0.49		120	0.58	0.50
90	0.64	0.56		90	0.65	0.57
60	0.70	0.63		60	0.71	0.64
30	0.74	0.71		30	0.75	0.71
15	0.76	0.74		15	0.77	0.75

Cath	node Side	d Cooling	
	ΔZ_{th} (z)		
θ°	sine.	rect.	
180	0.51	0.36	
120	0.58	0.50	
90	0.65	0.57	
60	0.71	0.64	
30	0.75	0.71	
15	0.77	0.75	

Fig.9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

www.dynexsemi.com 6/10





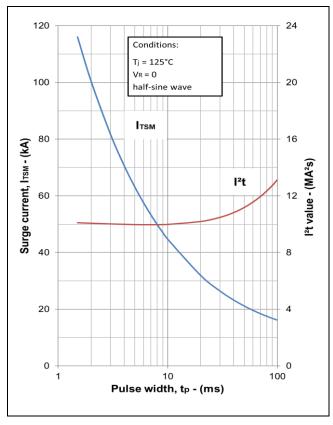


Fig. 10 Multi-cycle surge current

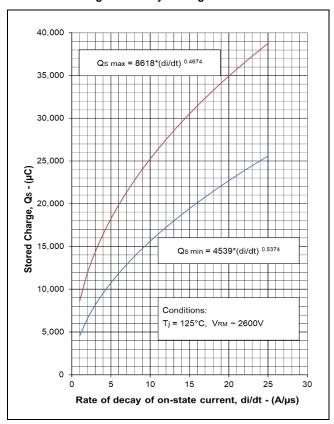


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

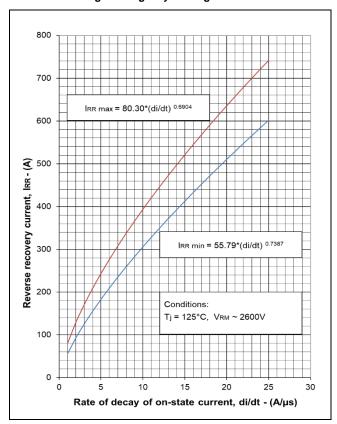


Fig. 13 Reverse recovery current

www.dynexsemi.com 7/10



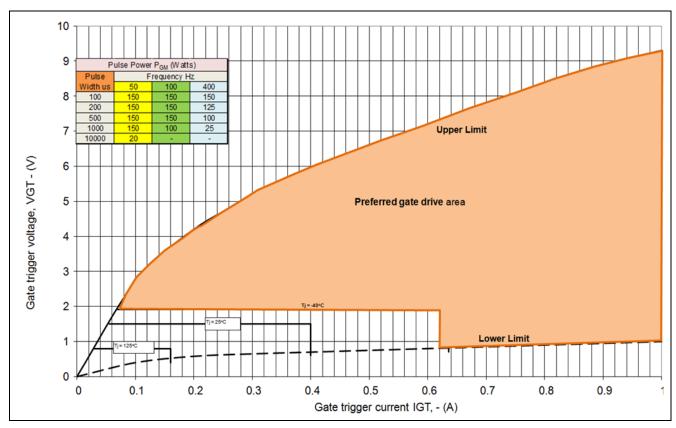


Fig.14 Gate characteristics

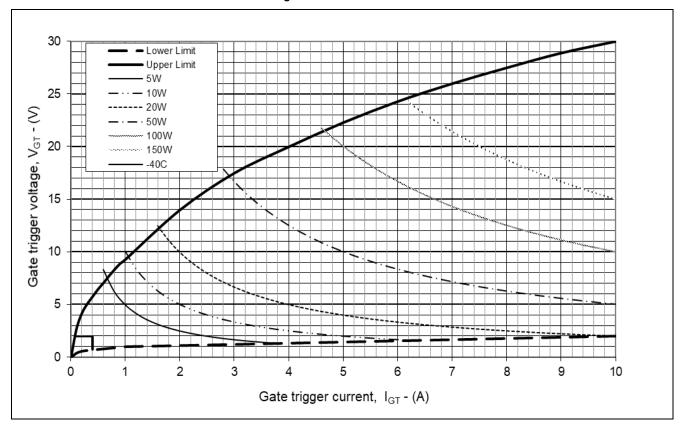


Fig. 15 Gate characteristics

www.dynexsemi.com 8/10



PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

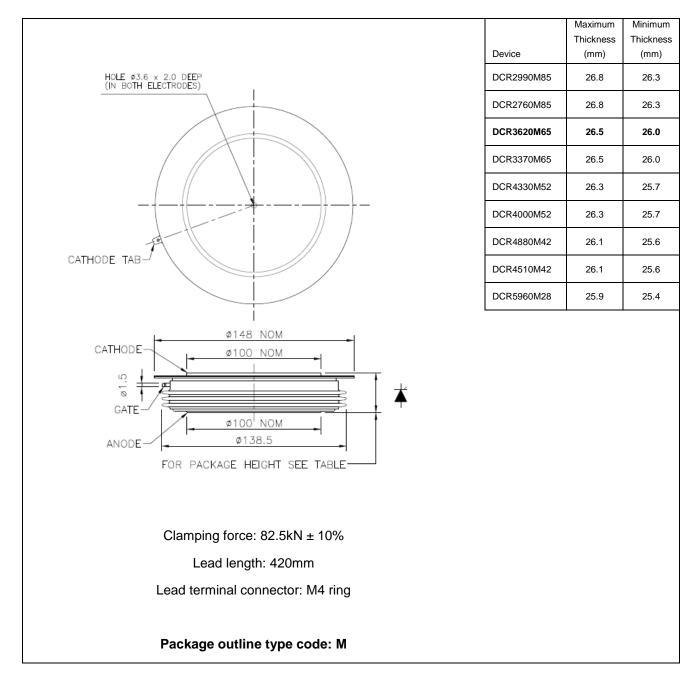


Fig. 16 Package outline

www.dynexsemi.com 9/10



IMPORTANT INFORMATION:

This publication is provided for information only and not for resale.

The products and information in this publication are intended for use by appropriately trained technical personnel.

Due to the diversity of product applications, the information contained herein is provided as a general guide only and does not constitute any guarantee of suitability for use in a specific application. The user must evaluate the suitability of the product and the completeness of the product data for the application. The user is responsible for product selection and ensuring all safety and any warning requirements are met. Should additional product information be needed please contact Customer Service.

Although we have endeavoured to carefully compile the information in this publication it may contain inaccuracies or typographical errors. The information is provided without any warranty or guarantee of any kind.

This publication is an uncontrolled document and is subject to change without notice. When referring to it please ensure that it is the most up to date version and has not been superseded.

The products are not intended for use in applications where a failure or malfunction may cause loss of life, injury or damage to property. The user must ensure that appropriate safety precautions are taken to prevent or mitigate the consequences of a product failure or malfunction.

The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

Product Status & Product Ordering:

We annotate datasheets in the top right hand corner of the front page, to indicate product status if it is not yet fully approved for production. The annotations are as follows:

Target Information: This is the most tentative form of information and represents a very preliminary specification.

No actual design work on the product has been started.

Provisional Information: Some initial development work has been performed. The datasheet represents a view of the

end product based on very limited information. Certain details will change.

Preliminary Information: The product design is complete and final characterisation for volume production is in progress.

The datasheet represents the product as it is now understood but details may change.

No Annotation: The product has been approved for production and unless otherwise notified by Dynex any

product ordered will be supplied to the current version of the data sheet prevailing at the

time of our order acknowledgement.

All products and materials are sold and services provided subject to Dynex's conditions of sale, which are available on request.

Any brand names and product names used in this publication are trademarks, registered trademarks or trade names of their respective owners.

HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED Doddington Road, Lincoln, Lincolnshire. LN6 3LF United Kingdom.

Phone: +44 (0) 1522 500500

Fax: +44 (0) 1522 500550

Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901

e-mail: powersolutions@dynexsemi.com

© Dynex Semiconductor Ltd. Technical Documentation – Not for resale.

www.dynexsemi.com 10/10